

IN THE CLAIMS

Complete listing of the claims:

1. (Currently amended) A semiconductor device comprising:
 - a silicon substrate;
 - an interface layer provided on the silicon substrate, the interface layer comprising a metal silicate;
 - a diffusion suppressing layer provided on the interface layer; and
 - a high dielectric constant insulating film provided on the diffusion suppressing layer;
wherein the diffusion suppressing layer comprises nitrogen and a high-k metal element different from a metal constitutional element of the high dielectric constant insulating film.
2. (Previously presented) A semiconductor device as in claim 1, wherein the interface layer has an equivalently converted SiO₂ thickness of 1.0 nm or smaller.
3. (Currently amended) A semiconductor device as in claim 1, wherein a high dielectric constant metal constitutional element of the high dielectric constant insulating film is the same as a high dielectric constant metal constitutional element of the interface layer.
4. (Currently amended) A method for manufacturing a semiconductor device comprising:
 - forming, on one surface of a silicon substrate, an initial layer which is a high dielectric constant metal element film for being mutually diffused with silicon in the silicon substrate;
 - forming a diffusion suppressing layer on the surface of the initial layer;
 - performing heat treatment to allow the high dielectric constant metal element film of the initial layer to be mutually diffused with silicon in the silicon substrate, thereby forming an interface layer comprising a metal silicate; and
 - forming a high dielectric constant insulating film on the surface of the diffusion suppressing layer;
 - wherein the diffusion suppressing layer comprises nitrogen and a high-k metal element different from a metal constitutional element of the high dielectric constant insulating film.
5. (Currently amended) A method for manufacturing a semiconductor device

comprising:

forming, on one surface of a silicon substrate, an initial layer which is a high dielectric constant metal element film for being mutually diffused with silicon in the silicon substrate;

forming a diffusion suppressing layer on the surface of the initial layer;

forming a high dielectric constant insulating film on the surface of the diffusion suppressing layer; and

performing heat treatment to allow the high dielectric constant metal element film of the initial layer to be mutually diffused with silicon in the silicon substrate, thereby forming an interface layer comprising a metal silicate;

wherein the diffusion suppressing layer comprises nitrogen and a high-k metal element different from a metal constitutional element of the high dielectric constant insulating film.

6. (Currently amended) A semiconductor device as in claim 2, wherein a high dielectric constant metal constitutional element of the high dielectric constant insulating film is the same as a high dielectric constant metal constitutional element of the interface layer.

7. (New) A semiconductor device as in claim 1, wherein the silicon substrate immediately below the interface layer and the high dielectric constant insulating film comprise a same metal constitutional element.

8. (New) A method as in claim 4, wherein the silicon substrate immediately below the interface layer and the high dielectric constant insulating film comprise a same metal constitutional element.

9. (New) A method as in claim 5, wherein the silicon substrate immediately below the interface layer and the high dielectric constant insulating film comprise a same metal constitutional element.